NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open

Rev. 01 — 10 March 2006

**Product data sheet** 

#### **Product profile** 1.

### **1.1 General description**

NPN Resistor-Equipped Transistors (RET) family in Surface Mounted Device (SMD) plastic packages.

#### Table 1. **Product overview**

Type number	Package	Package		
	Philips	JEITA	JEDEC	
PDTC123TE	SOT416	SC-75	-	PDTA123TE
PDTC123TK	SOT346	SC-59A	TO-236	PDTA123TK
PDTC123TM	SOT883	SC-101	-	PDTA123TM
PDTC123TS <sup>[1]</sup>	SOT54	SC-43A	TO-92	PDTA123TS
PDTC123TT	SOT23	-	TO-236AB	PDTA123TT
PDTC123TU	SOT323	SC-70	-	PDTA123TU

Reduces component count

in digital applications

Switching loads

Reduces pick and place costs

Cost-saving alternative for BC847 series

[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 100 mA output current capability

### 1.3 Applications

- Digital applications
- Control of IC inputs

### 1.4 Q

### Та

Quick r	eference data					
Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V

V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ

# PHILIPS

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### 2. Pinning information

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		
3	GND (emitter)	001aab347	1 R1 006aaa218
SOT54A			
1	input (base)		
2	output (collector)		
3	GND (emitter)	001aab348	1 R1 S 006aaa218
SOT54 va	riant		
1	input (base)		
2	output (collector)	The second secon	
3	GND (emitter)	U U U U U U U U U U U U U U U U U U U	1 R1 006aaa218
SOT23; S	OT323; SOT346; SOT416		
1	input (base)		
2	GND (emitter)	3	
3	output (collector)	1 2 006aaa144	1 2 sym012
SOT883			
1	input (base)		
2	GND (emitter)		
3	output (collector)	2 Transparent top view	

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### 3. Ordering information

Table 4. Orde	ring informa	ation					
Type number	Package	age					
	Name	Description	Version				
PDTC123TE	SC-75	plastic surface mounted package; 3 leads	SOT416				
PDTC123TK	SC-59A	plastic surface mounted package; 3 leads	SOT346				
PDTC123TM	SC-101	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm	SOT883				
PDTC123TS <sup>[1]</sup>	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54				
PDTC123TT	-	plastic surface mounted package; 3 leads	SOT23				
PDTC123TU	SC-70	plastic surface mounted package; 3 leads	SOT323				

[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

### 4. Marking

Marking code <sup>[1]</sup>
2B
GB
FB
TC123T
ZM*
*1T

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

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### 5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
lo	output current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT416		<u>[1]</u> _	150	mW
	SOT346		<u>[1]</u> _	250	mW
	SOT883		[2][3]	250	mW
	SOT54		<u>[1]</u> -	500	mW
	SOT23		<u>[1]</u> _	250	mW
	SOT323		<u>[1]</u> _	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 60 µm copper strip line, standard footprint.

### 6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> _	-	833	K/W
	SOT346		<u>[1]</u> _	-	500	K/W
	SOT883		[2][3]	-	500	K/W
	SOT54		<u>[1]</u> _	-	250	K/W
	SOT23		<u>[1]</u> _	-	500	K/W
	SOT323		<u>[1]</u> _	-	625	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

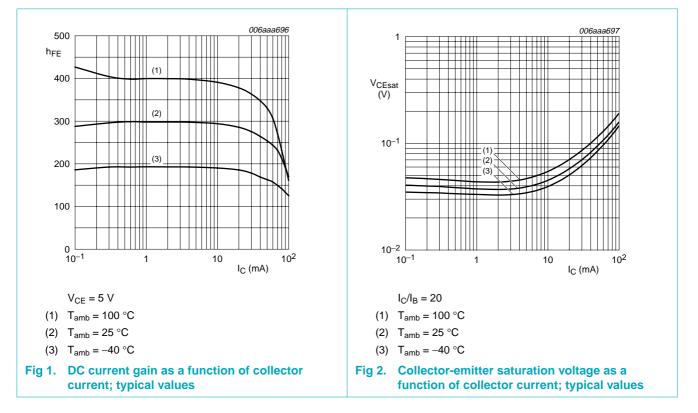
[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 60  $\mu m$  copper strip line, standard footprint.

NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open

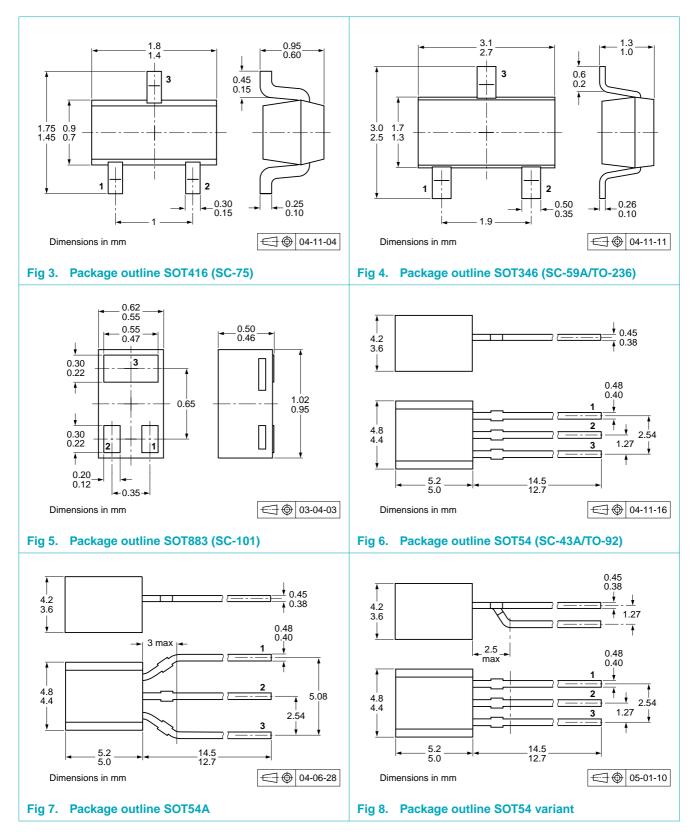
### 7. Characteristics

°C unless otherwise spec	cified.				
Parameter	Conditions	Min	Тур	Max	Unit
collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub> collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	1	μA
	$\label{eq:Vce} \begin{array}{l} V_{CE} = 30 \; V; \; I_{B} = 0 \; A; \\ T_{j} = 150 \; ^{\circ}C \end{array}$	-	-	50	μA
emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 20 mA	30	-	-	
collector-emitter saturation voltage	$I_{C}$ = 10 mA; $I_{B}$ = 0.5 mA	-	-	150	mV
bias resistor 1 (input)		1.54	2.2	2.86	kΩ
collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
	<ul> <li>C unless otherwise spect</li> <li>Parameter</li> <li>collector-base cut-off current</li> <li>collector-emitter cut-off current</li> <li>emitter-base cut-off current</li> <li>DC current gain</li> <li>collector-emitter saturation voltage</li> <li>bias resistor 1 (input)</li> </ul>	$^{\circ}C$ unless otherwise specified.ParameterConditionscollector-base cut-off current $V_{CB} = 50 \text{ V}; \text{ I}_E = 0 \text{ A}$ collector-emitter cut-off current $V_{CE} = 30 \text{ V}; \text{ I}_B = 0 \text{ A}$ collector-emitter cut-off current $V_{CE} = 30 \text{ V}; \text{ I}_B = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$ emitter-base cut-off current $V_{EB} = 5 \text{ V}; \text{ I}_C = 0 \text{ A}$ DC current gain $V_{CE} = 5 \text{ V}; \text{ I}_C = 20 \text{ mA}$ collector-emitter saturation voltage $I_C = 10 \text{ mA}; \text{ I}_B = 0.5 \text{ mA}$ bias resistor 1 (input) $V_{CB} = 10 \text{ V}; \text{ I}_E = \text{ i}_e = 0 \text{ A};$	$^{\circ}C$ unless otherwise specified.MinParameterConditionsMincollector-base cut-off current $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$ $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$ $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 ^{\circ}C$ -emitter-base cut-off current $V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$ $T_c = 150 ^{\circ}C$ -DC current gain $V_{CE} = 5 \text{ V}; I_C = 20 \text{ mA}$ 30collector-emitter saturation voltage $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ $I_c = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ -	$^{\circ}C$ unless otherwise specified.MinTypParameterConditionsMinTypcollector-base cut-off current $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$ $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$ $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 \circ \text{C}$ -collector-emitter cut-off current $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 \circ \text{C}$ -emitter-base cut-off current $V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$ $T_j = 150 \circ \text{C}$ -DC current gain $V_{CE} = 5 \text{ V}; I_C = 20 \text{ mA}$ 30DC current gain $V_{CE} = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ saturation voltage-bias resistor 1 (input)1.542.2collector capacitance $V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ $$	$^{\circ}C$ unless otherwise specified.MinTypMaxCollector-base cut-off current $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$ $CB = 50 \text{ V}; I_E = 0 \text{ A}$ 100collector-emitter cut-off current $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$ $T_j = 150 ^{\circ}C$ 100emitter-base cut-off current $V_{CE} = 30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 ^{\circ}C$ 100DC current gain $V_{CE} = 5 \text{ V}; I_C = 0 \text{ A}$ $CE = 5 \text{ V}; I_C = 20 \text{ mA}$ 30DC current gain $V_{CE} = 5 \text{ V}; I_C = 20 \text{ mA}$ 30150bias resistor 1 (input) $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ collector capacitance1.542.22.86

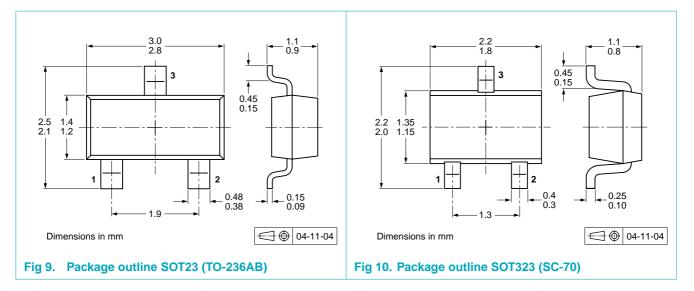


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### 8. Package outline



NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open



### 9. Packing information

### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packin	Packing quantity		
			3000	5000	10000	
PDTC123TE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC123TK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC123TM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315	
PDTC123TS	SOT54	bulk, straight leads	-	-412	-	
	SOT54A	tape and reel, wide pitch	-	-	-116	
		tape ammopack, wide pitch	-	-	-126	
	SOT54 variant	bulk, delta pinning	-	-112	-	
PDTC123TT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
PDTC123TU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

[1] For further information and the availability of packing methods, see Section 12.

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### **10. Revision history**

Table 10. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC123T_SER_1	20060310	Product data sheet	-	-

### **11. Legal information**

### 11.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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# **PDTC123T series**

NPN resistor-equipped transistors; R1 = 2.2 kΩ, R2 = open

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